Abstracts

Sheet Resistance Measurements of Implanted Layers on Silicon Wafers Using a Microwave Resistivity Probe

M.S. Wang, H. Bhimnathwala, S.S. Yao and J.M. Borrego. "Sheet Resistance Measurements of Implanted Layers on Silicon Wafers Using a Microwave Resistivity Probe." 1991 MTT-S International Microwave Symposium Digest 91.3 (1991 Vol. III [MWSYM]): 1137-1140.

In this paper we present the use of microwave radiation at 35 GHz from an open ended waveguide for measuring the sheet resistance of implanted layers on high resistivity silicon with dynamic range and spatial resolution comparable to the one of four point probes. The technique is capable of measuring implanted layers with doses in the range of 10/sup 12/ ions/cm² to 10/sup 16/ ions/cm².

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